

**Physical bases of dental materials**  
10.  
Thermal and electric properties

e-book chapter.:  
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### Thermal properties

- temperature
- heat uptake/release

specific heat of dental materials:

material	c (J/(kg·K))
enamel	750
dentine	1260
water	4190
amalgam	210
gold	126
porcelain	1100
glass	800
PMMA	1460
zinc-phosphate	500

heat capacity ( $C$ ): 
$$C = \frac{\Delta Q}{\Delta T}$$

molar heat capacity ( $c_V$ ): 
$$c_V = \frac{C}{V}$$

specific heat capacity ( $c$ ): 
$$c = \frac{C}{m}$$

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• heat conduction

- lattice vibrations
- free electrons

$$\frac{\Delta Q}{\Delta t} = -\lambda A \frac{\Delta T}{\Delta x}$$
 Fourier's law

thermal conductivity of dental materials

material	$\lambda$ (W/(mK))
enamel	0,9
dentine	0,6
water	0,44
amalgam	23
gold	300
porcelain	1
water	0,6-1,4
acrylate	0,2
PMMA	0,2-0,3
zinc-phosphate	1,2

$\lambda$  — thermal conductivity  
 $J/(s \cdot m^2 \cdot K/m) = W/(m \cdot K)$

used in case of stationary conditions

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non-stationary conditions:

thermal diffusivity of dental materials

$$D = \frac{\lambda}{c \cdot \rho}$$

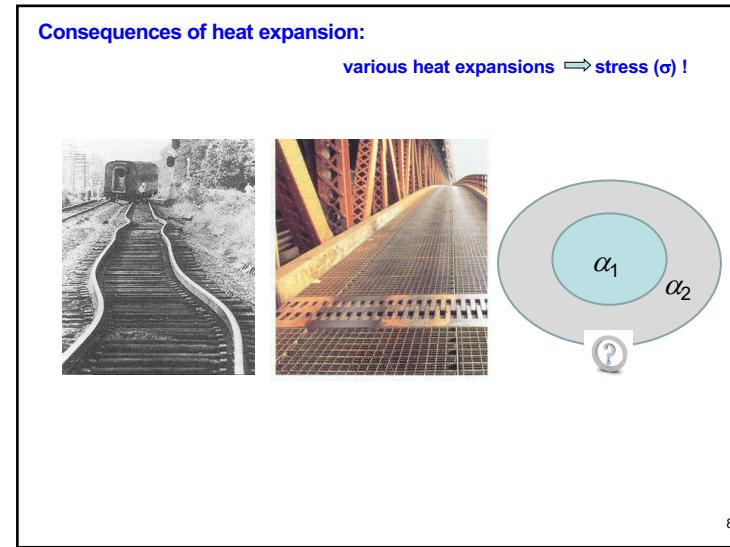
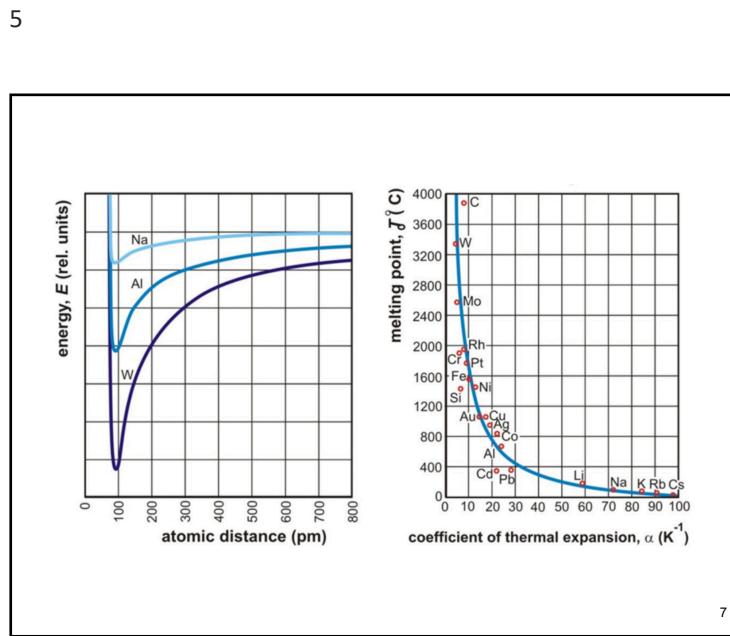
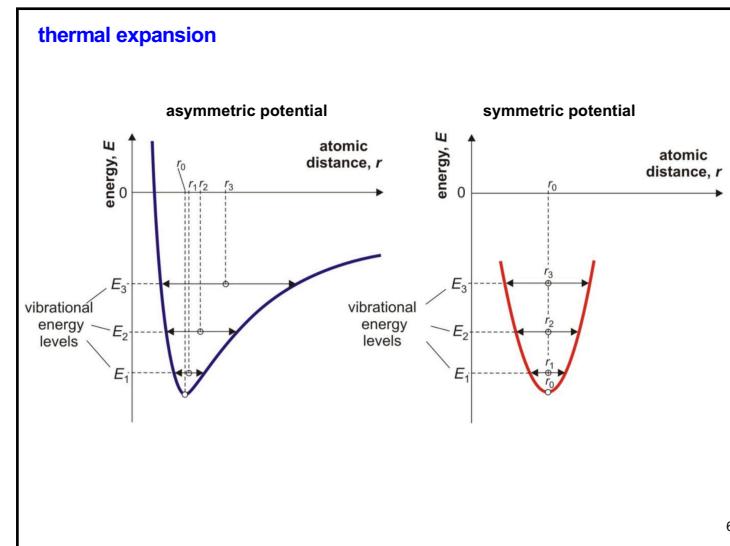
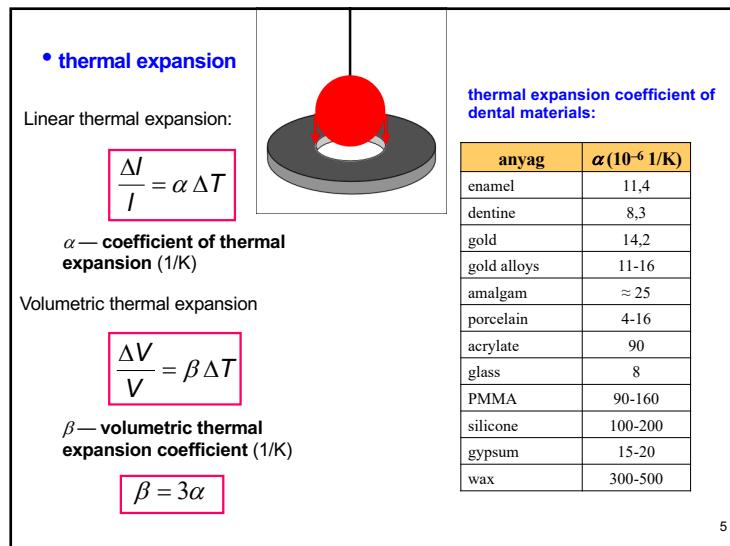
D — thermal diffusivity  
 $(m^2/s)$

material	$\lambda$ (W/(mK))	$D$ ( $10^{-6} m^2/s$ )
enamel	0,9	0,5
dentine	0,6	0,2
water	0,44	0,14
amalgam	23	9,6
gold	300	118
porcelain	1	0,4
water	0,6-1,4	0,3-0,7
acrylate	0,2	0,1
PMMA	0,2-0,3	0,12
zinc-phosphate	1,2	0,3

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## Electricity



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## Electric charge

**Charge:** intrinsic property (like mass).  
Macroscopic bodies are usually neutral.



electron (*ηλεκτρόνιον*) = amber

Electron negative, proton positive charge.

Electric charge is quantizes, its smallest unit is the **elementary charge ( $e$ )**, that is the charge of a proton.  
Unit: 1 C (Coulomb) = 1 A·s

$$e = |e^-| = 1,6 \cdot 10^{-19} \text{ C}$$

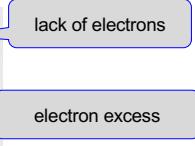
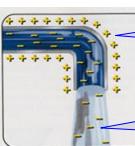
Faraday-constant (total charge of 1 mol protons):

$$F = 1,6 \cdot 10^{-19} \text{ C} \cdot 6 \cdot 10^{23} \text{ 1/mol} = 96\,500 \text{ C/mol}$$

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## Charge separation

Charges can be separated by rubbing (static electricity)



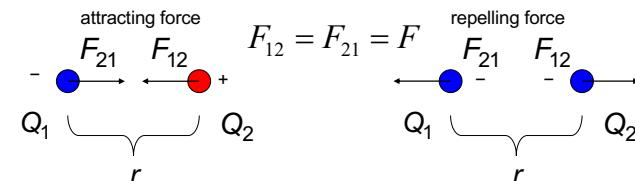
charge separation followed by discharge!

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## Electric interaction

Bodies with electric charge interact with each other:

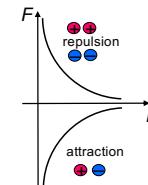
- unlike charges attract
- like charges repel



Coulomb-force:

$$F = k \frac{Q_1 Q_2}{r^2}$$

$$k = 9 \cdot 10^9 \text{ Nm}^2/\text{C}^2$$



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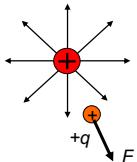
## Electric field, field lines

If the interaction is present without close contact, a field is present that transmits the force between the bodies.

The field is described by the field strength and represented by the field lines.

**electric field strength,  $E$ :**

$$E = \frac{F}{q} \quad \left[ \frac{N}{C} \right]$$

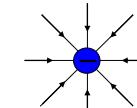
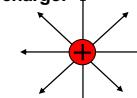


**field lines:**

- Direction shows the direction of field
- density shows the field strength

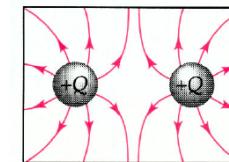
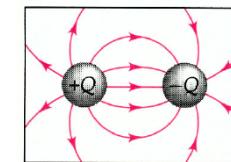
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**Field of a point charge:**



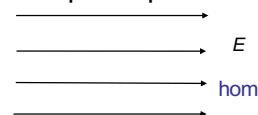
inhomogeneous field

**field of a dipole and two like charges**



inhomogeneous field

**field between the plates of a planar capacitor**



$E$

homogeneous field

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## Voltage (= potential difference)

The work of  $W_{1 \rightarrow 2}$  is required to move a  $q$  point charge between point 1 and point 2 of the field. The  $W_{1 \rightarrow 2} / q$  ratio is independent on the magnitude of charge and the path of movement. Thus:

**Electric voltage** between point 1 and point 2 is:

$$U_{21} = \frac{W_{1 \rightarrow 2}}{q}$$

Unit: Volt [V]

$$1 \text{ V} = \frac{1 \text{ J}}{1 \text{ C}}$$

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## Electric potential

$W_{0 \rightarrow i}$  represents the work that is required to move a charge of  $q$  from a standard 0 point to point  $i$ .

$\frac{W_{0 \rightarrow i}}{q}$  independent of charge and path of movement!

$$\text{Electric potential: } \varphi_i = \frac{W_{0 \rightarrow i}}{q} \quad \text{Unit: Volt (V)}$$

Electric potential gives the potential energy of the 1 C charge at point  $i$ , after it has been moved there from the standard 0 point.

Often the standard point is at infinity, thus:

$$\varphi_i = \frac{W_{\infty \rightarrow i}}{q}$$

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## Electric current

Directed transport of charge carriers  
 charge carriers = freely moving, electrically charged particles  
 example in metals: **electrons**  
 example in electrolytes or gases: **ions**

### Electric current ( $I$ ):

$$I = \frac{\Delta Q}{\Delta t}$$

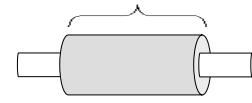
$\Delta Q$ : charge passing through the cross section of a conductor in  $\Delta t$  time

unit: ampere (A),  $1A = 1C/1s$

Technical current direction: direction of movement of positive charge carriers.

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## Ohm's law



Potential difference ( $U$ ) and current ( $I$ ) are directly proportional

$$U \sim I$$

$$U = RI$$

$R$ : resistance

$G$ : conductance

$$R = \frac{U}{I}$$

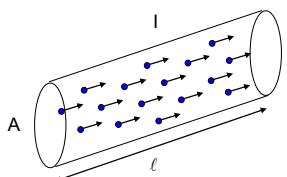
unit: ohm ( $\Omega$ )  $1\Omega = \frac{1V}{1A}$

$$G = \frac{1}{R}$$

unit: siemens (S),  $1S = \frac{1}{1\Omega}$

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## Resistance of a conductor



$$\left. \begin{aligned} I &\sim \frac{A}{l} U \\ I &= \frac{U}{R} \end{aligned} \right\} R \sim \frac{l}{A} \Rightarrow R = \rho \frac{l}{A}$$

resistivity  
 SI-unit:  $\Omega m$

$$\text{conductivity } (\sigma): \quad \sigma = \frac{1}{\rho}$$

SI-unit: S/m

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- **resistivity**  
 or specific resistance ( $\rho$ ):

$$\rho = \frac{R \cdot A}{l} \quad (\Omega m)$$

- **conductivity ( $\sigma$ )**:

$$\sigma = \frac{1}{\rho} \quad ((\Omega m)^{-1} = S/m)$$

material	$\sigma$ (S/m)
silver	$6,8 \cdot 10^7$
gold	$4,3 \cdot 10^7$
platinum	$0,94 \cdot 10^7$
germanium	2,2
silicon	$4 \cdot 10^{-4}$
cirkonia	$\approx 10^{-10}$
porcelain	$\approx 10^{-11}$
glass	$\approx 10^{-13}$
PMMA	$\approx 10^{-12}$
PE	$\approx 10^{-16}$

conductors  
 semi conductors  
 insulators

Depends on:

- quantity of free charge carriers (electrons, ions)
- mobility of charge carriers

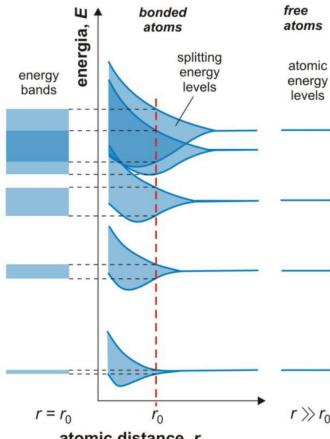
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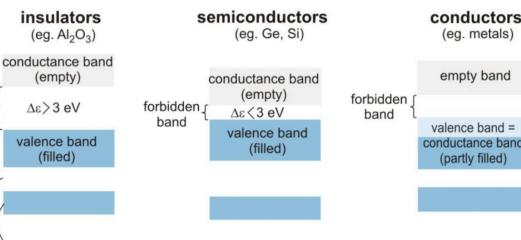
## Electric structure of solid bodies

Bands fill according to:

- energy minimum
- Pauli-principle
- number of electrons



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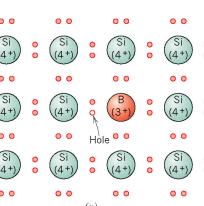
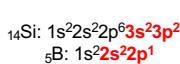
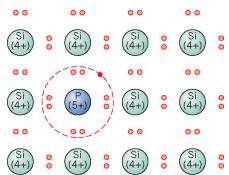
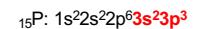
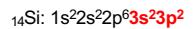
f.e. NaI ( $\Delta\varepsilon = 5$  eV)  
Si ( $\Delta\varepsilon = 1,1$  eV)  
Ge ( $\Delta\varepsilon = 0,7$  eV)

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## Intrinsic semiconductors

### Doped semiconductors



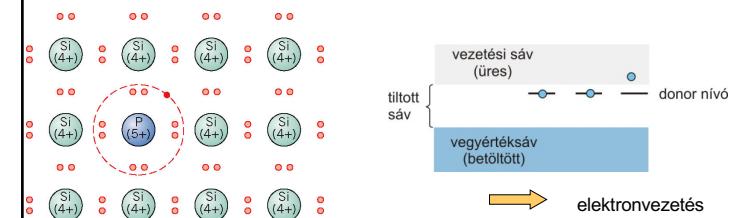
(a)

## Szennyezett félvezető

alapkristály pl. Si  
 $^{14}\text{Si}: 1s^2 2s^2 2p^6 3s^2 3p^2$

*n*-félvezető

adalék pl. P  
 $^{15}\text{P}: 1s^2 2s^2 2p^6 3s^2 3p^3$



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Szenyezett félvezető

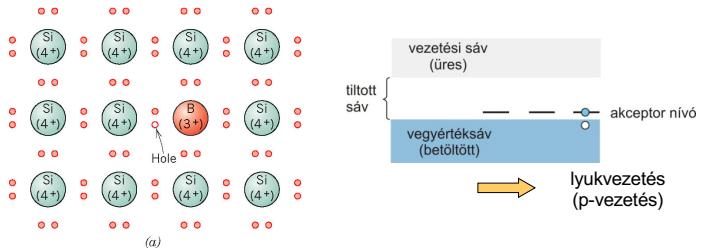
alapkristály pl. Si

${}_{14}\text{Si}: 1\text{s}^2 2\text{s}^2 2\text{p}^6 3\text{s}^2 3\text{p}^2$

*p*-félvezető

adalék pl. B

${}_5\text{B}: 1\text{s}^2 \mathbf{2\text{s}^2 2\text{p}^1}$



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